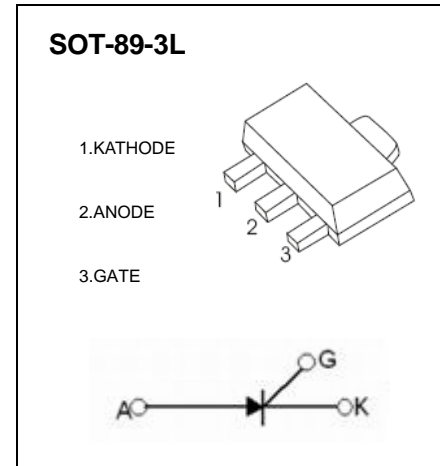


Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier

FEATURES

- Current- I_{GT} : 200 μ A
- I_{TRMS} : 0.8 A
- V_{RRM}/V_{DRM} : MCR100-6: 400 V
MCR100-8: 600 V
- Operating and storage junction temperature range
 T_J, T_{stg} : -55 $^{\circ}$ C to +150 $^{\circ}$ C



ELECTRICAL CHARACTERISTICS (Ta=25 $^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage	V_{TM}^*	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V_{DRM} AND V_{RRM}	$I_{DRM}=10\mu A$	400 600		V	
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}=\text{Rated}$ V_{DRM} or V_{RRM}		10	μ A	
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA	
Gate trigger current	I_{GT}	$V_{AK}=7V$	A2	5	15	μ A
			A1	15	30	μ A
			A	30	80	μ A
			B	80	200	μ A

* Forward current applied for 1 ms maximum duration, duty cycle \leq 1%.



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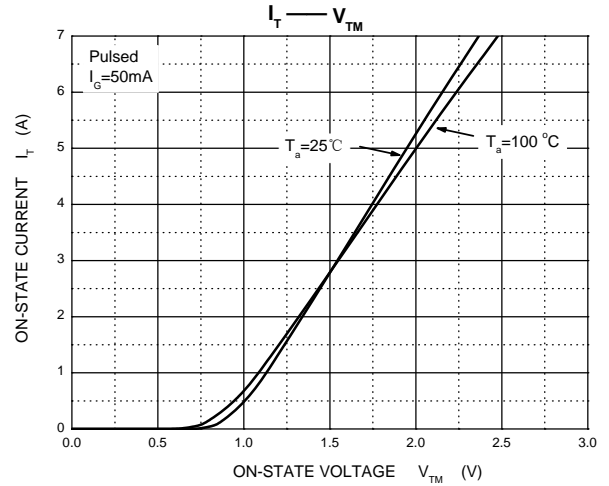
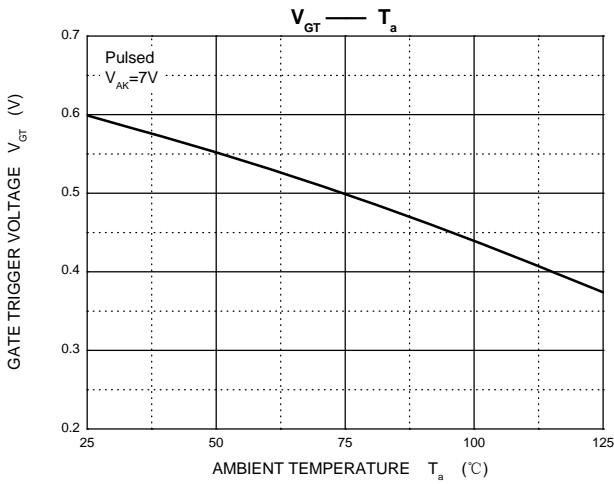
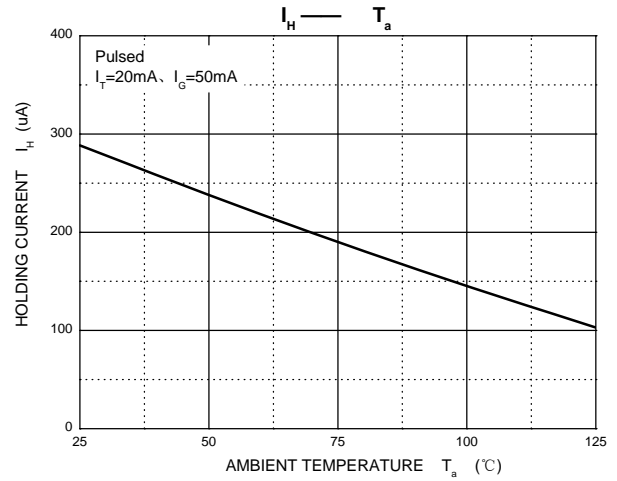
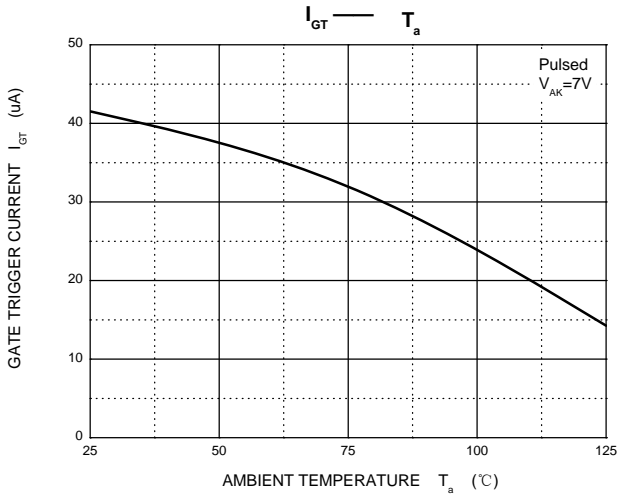
SOT-89



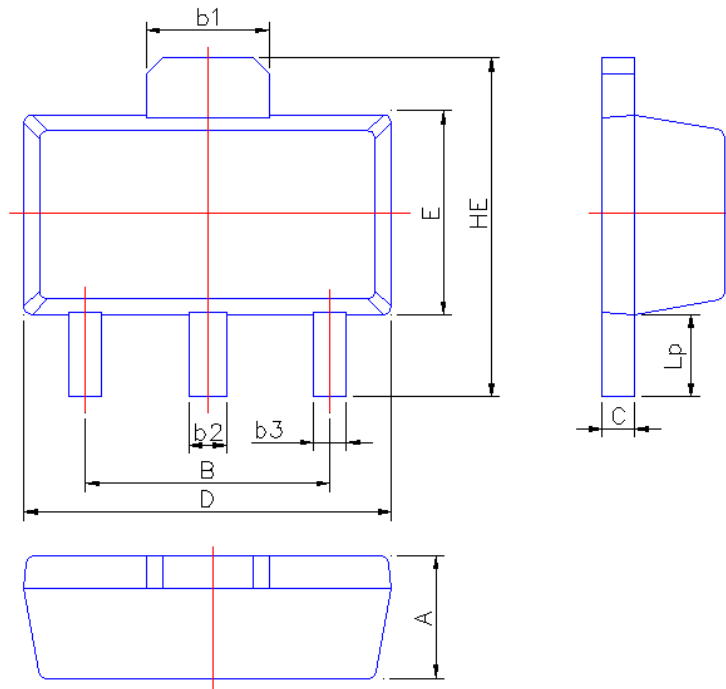
MCR100-6U-8U

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Typical Characteristics



SOT-89 PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	1.40	1.60
B	2.95	3.05
b1	1.45	1.70
b2	0.45	0.56
b3	0.35	0.50
C	0.35	0.50
D	4.40	4.60
E	2.35	2.55
HE	3.90	4.40
Lp	0.90	1.10